

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9. (Canceled)

10. (New) A mask blank, which is an original plate for manufacturing a transfer mask, comprising:

    a substrate including a main surface, and a substrate peripheral edge having an unnecessary region;

    a thin film formed on the main surface of the substrate;

    a resist film formed on the thin film; and

    a supported region of the mask blank, the supported region being located inside the unnecessary region of the substrate peripheral edge on the main surface of the substrate, and the supported region being a region supported by a substrate holding member of an exposure device when a transfer is carried out by using the transfer mask,

    wherein the resist film is not formed in the supported region of the mask blank.

11. (New) The mask blank according to claim 10, further comprising

    an auxiliary pattern forming region for an auxiliary pattern formed on the transfer mask when the transfer mask is manufactured from the mask blank, the auxiliary pattern forming region being located inside the unnecessary region,

    wherein the thin film and the resist film are formed on the auxiliary pattern forming region.

12. (New) The mask blank according to claim 10, wherein the resist film is a positive resist.

13. (New) The mask blank according to claim 10, wherein the resist film is not formed on the unnecessary region.

14. (New) A mask blank, which is an original plate for manufacturing a transfer mask, comprising:

    a substrate, including a main surface, and a substrate peripheral edge having an unnecessary region;

    a thin film formed on the main surface of the substrate;

    a positive resist film formed on the thin film; and

    a supported region of the mask blank, the supported region being located inside the unnecessary region of the substrate peripheral edge on the main surface of the substrate, and the supported region being a region supported by a substrate holding member of an exposure device when a transfer is carried out by using the transfer mask,

    wherein the positive resist film in the supported region of the mask blank is exposed to light, so as to remove the positive resist film in the supported region when the positive resist film is developed.

15. (New) The mask blank according to claim 14, further comprising an auxiliary pattern forming region for an auxiliary pattern that is formed on the transfer mask when the transfer mask is manufactured from the mask blank, the auxiliary pattern forming region being located inside the unnecessary region,

    wherein the auxiliary pattern forming region is a non-exposure region not exposed to light.

16. (New) The mask blank according to claim 14, wherein the resist film is not formed on the unnecessary region.

17. (New) A manufacturing method of a mask blank, which is an original plate for manufacturing a transfer mask, the method comprising:

forming a thin film on a main surface of a substrate, the substrate including a substrate peripheral edge having an unnecessary region;

applying a positive resist on the thin film to form a positive resist film; and exposing the positive resist film on a supported region of the mask blank to light, so as to remove the positive resist film when the positive resist film is developed,

wherein the supported region of the mask blank, which is located inside the unnecessary region of the substrate peripheral edge on the main surface of the substrate, is a region to be supported by a substrate holding member of an exposure device when a transfer is carried out by using the transfer mask.

18. (New) The manufacturing method of the mask blank according to claim 17, further comprising:

exposing the positive resist film on the unnecessary region to light;  
supplying a developing solution selectively to the supported region and the unnecessary region exposed to light after exposing the positive resist film; and  
removing the positive resist film formed on the supported region and the unnecessary region.

19. (New) A manufacturing method of a transfer mask, comprising;  
preparing the mask blank according to claim 10; and  
forming a transfer pattern and removing the thin film formed on the supported region of the mask blank by carrying out an etching for manufacturing the transfer mask.

20. (New) A manufacturing method of a transfer mask, the method comprising:  
preparing the mask blank according to claim 14; and  
forming a transfer pattern and removing the thin film formed on the supported region of the mask blank by carrying out an etching for manufacturing the transfer mask.

21. (New) A transfer mask, the mask comprising:

a substrate including a main surface, and a substrate peripheral edge having an unnecessary region;

a thin film on the main surface of the substrate in which a transfer pattern is formed by a positive resist;

a supported region of the transfer mask, which is located inside an unnecessary region of the substrate peripheral edge on the main surface of the substrate, and is supported by a substrate holding member of an exposure device when a transfer is carried out by using the transfer mask,

wherein the thin film is not formed in the supported region of the transfer mask.

22. (New) A manufacturing method of a semiconductor device, comprising:
  - preparing the transfer mask according to claim 21;
  - supporting the supported region of the transfer mask with the substrate holding member of the exposure device; and
  - transferring the transfer pattern on a semiconductor substrate by a lithography method to form a pattern.